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Numerical Simulation and Control of Sublimation Growth of SiC Bulk Single Crystals: Modeling, Finite Volume Method, Analysis and Results

Peter Philip

Show & Tell at IMA Minneapolis, September 15, 2004

Joint work with:

- Jürgen Geiser, Olaf Klein, Jürgen Sprekels, Krzysztof Wilmański (Weierstrass Institute for Applied Analysis and Stochastics (WIAS), Berlin) (modeling, finite volume method)
- Christian Meyer, Fredi Tröltzsch (TU Berlin, Department of Mathematics) (optimal control)

Cooperation with:

• Klaus Böttcher, Detev Schulz, Dietmar Siche (Institute of Crystal Growth (IKZ), Berlin) (growth experiments)

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Applications of SiC bulk single crystals

Light-emitting diodes: Lifetime: ≈ 10 years Light extraction efficiency > 32 % (light bulb: ≈ 10 %)





Blue laser: Its application in the DVD player admits up to 10-fold capacity of disc

SiC-based electronics still works at 600 deg. Celsius, SiC sensors placed close to car engines can save resources and costs



SiC growth by physical vapor transport (PVT)



- polycrystalline SiC powder sublimates inside inductionheated graphite crucible at 2000 -3000 K and ≈ 20 hPa
- a gas mixture consisting of Ar (inert gas), Si, SiC₂, Si₂C, ... is created
- an SiC single crystal grows on a cooled seed

Problems:

- Needed: Perfect single crystals as large and as quick as possible (currently: Ø 5 – 10 cm, one growth run: 2 – 3 days)
- High energy costs, high costs for apparatus replacement (every 10 runs)



- Wrong control parameters (setup, position of induction coil, heating power) \Rightarrow (costly !) failure of growth run
- High temperatures prevent measurements inside growth apparatus ⇒ experimental optimization of process is difficult and costly



Goal:

Stationary and transient optimal control of process, using mathematical modeling, numerical simulation.

Model includes

- 1. Heat conduction in gas, graphite, powder, crystal
- 2. Radiative heat transfer between cavity surfaces (nonlocal integral operators)
- 3. Semi-transparency of crystal (band model)
- 4. Induction heating (Maxwell's equations)
- 5. Mass transport in gas, powder, graphite (Euler equations, porous media equations, ...)
- 6. Chemical reactions in gas (reaction-diffusion equations)
- Crystal growth, sublimation of source powder, decomposition of graphite walls (multiple free boundaries)

Mathematical results

- Discrete existence and uniqueness of a solution to a finite volumes scheme for the nonlinear (quasilinear), nonlocal heat transfer with mixed boundary conditions.
 Discrete L[∞]-L¹ a priori estimates.
- Discrete L[∞]-L[∞] a priori estimates, discrete maximum principle in the semilinear, nonlocal case.
- Existence of a (continuous) optimal control in the nonlocal, semilinear case (approximate a prescribed gradient field in the gas phase by controling the heat sources). Necessary optimality conditions were established.

Numerical results: Temperature evolution of the powder charge: $P_{\text{max}} = 7 \text{ kW}$



Numerical results: Optimization of temperature field



Thank You for Your Attention !

Publications / More Information:

http://www.ima.umn.edu/~philip/sic/#Publications
http://www.ima.umn.edu/~philip/sic/

- See poster during lunch session.
- Extended 1-hour talk tomorrow,

Applied Mathematics and Numerical Analysis Seminar School of Mathematics

Thu, Sep 16, 11:15 a.m., Vincent Hall 570.